

FIG.1

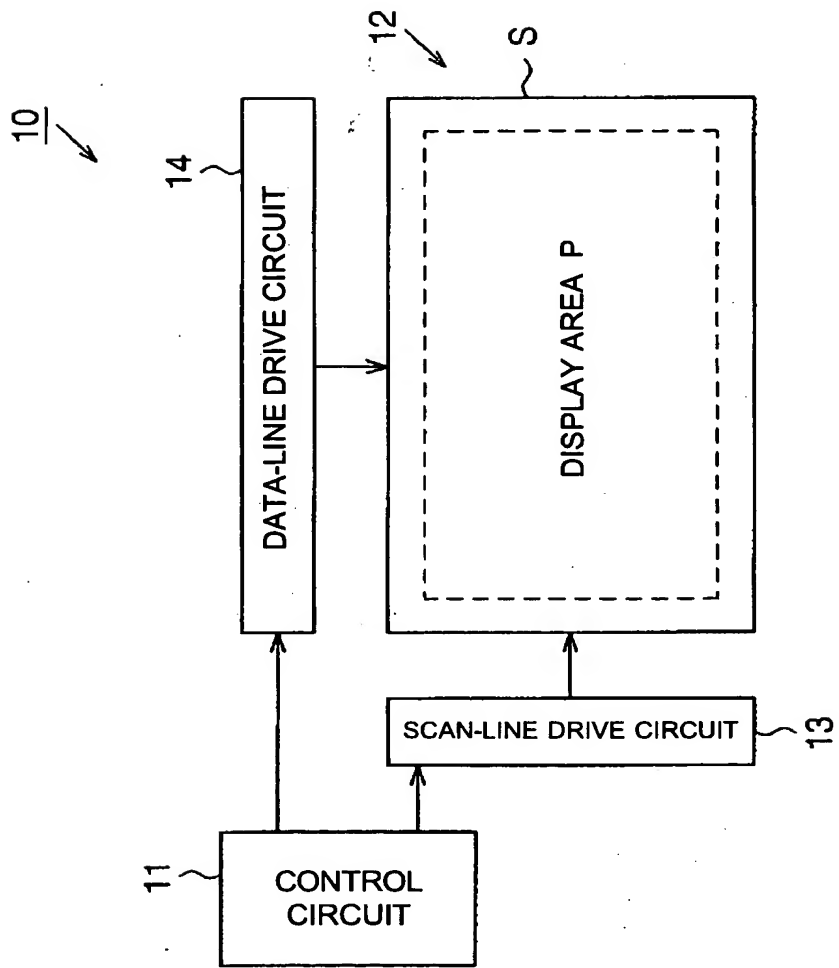


FIG. 2

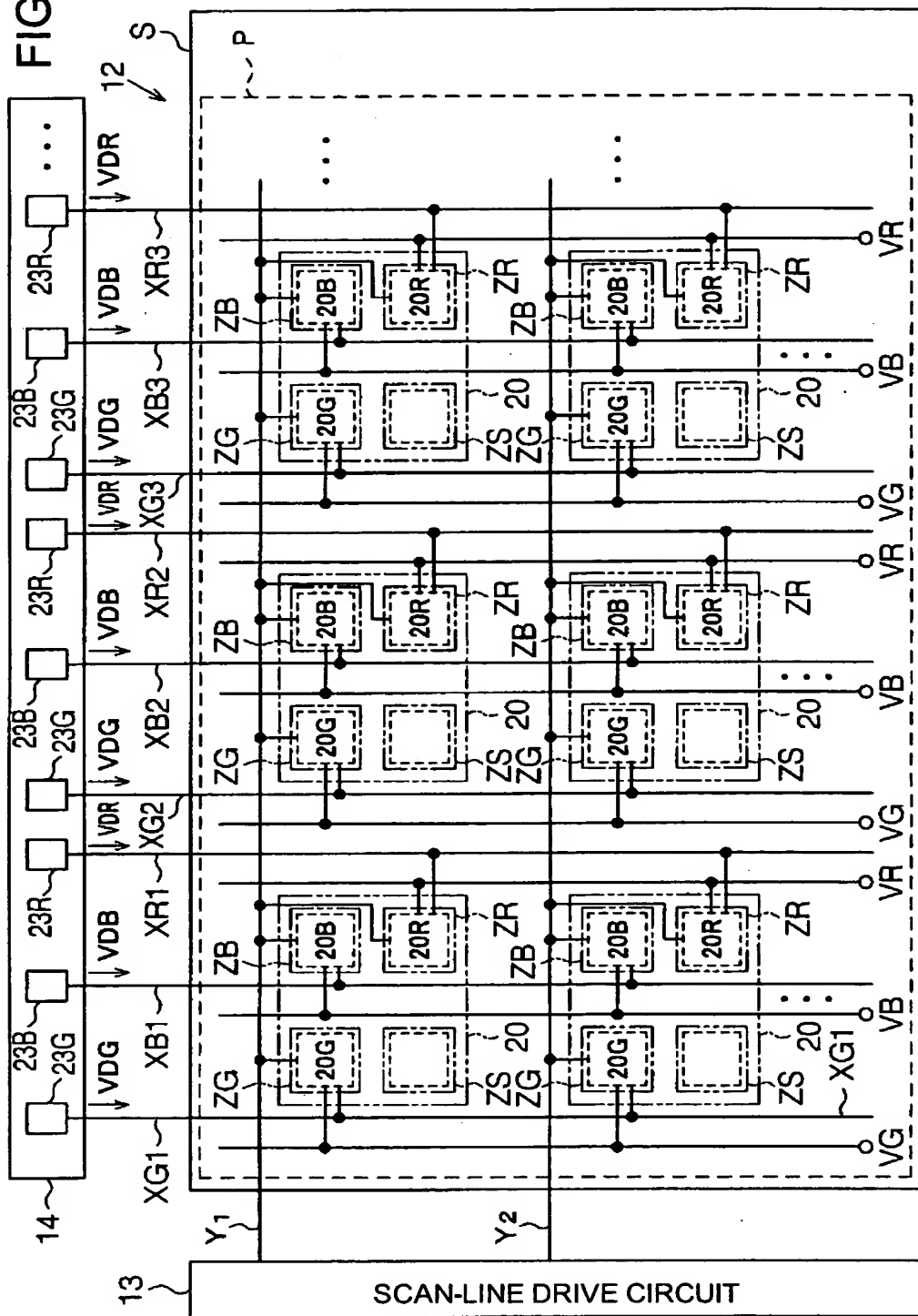
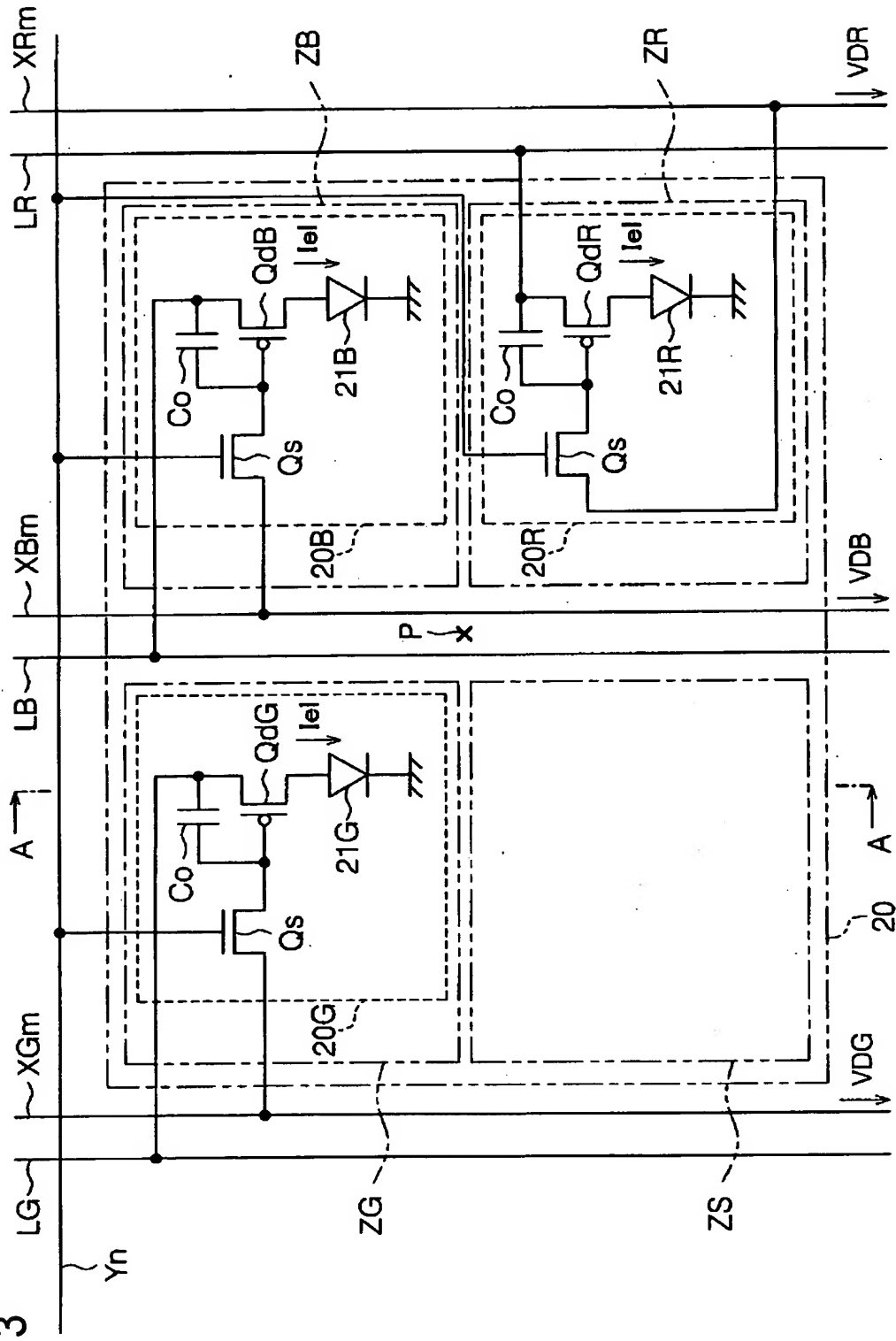


FIG.3



This cross-sectional diagram illustrates a multi-layered semiconductor structure. The top surface is labeled 12. A horizontal dimension ZG spans the left portion, while ZS spans the right portion. A vertical dashed line indicates a boundary between two main sections. On the left side, under ZG, there are several stacked layers: a bottom layer 38, followed by a patterned layer 36a, another patterned layer 36b, and a top layer 38. A region labeled LFG is located beneath the first patterned layer 36a. On the right side, under ZS, there are more layers: a bottom layer 32b, a middle layer 32a, and a top layer 38. This section also includes a patterned layer 34, a layer 35a, a layer 35b, and a layer 33D. A region labeled NLF is situated above the middle layer 32a. At the very bottom, a layer 33G is shown. A bracket labeled DZ encompasses the lower portion of both sides. On the far right, a large hatched area is labeled Sd. Other labels include T, 31a, 31b, 31, and S.

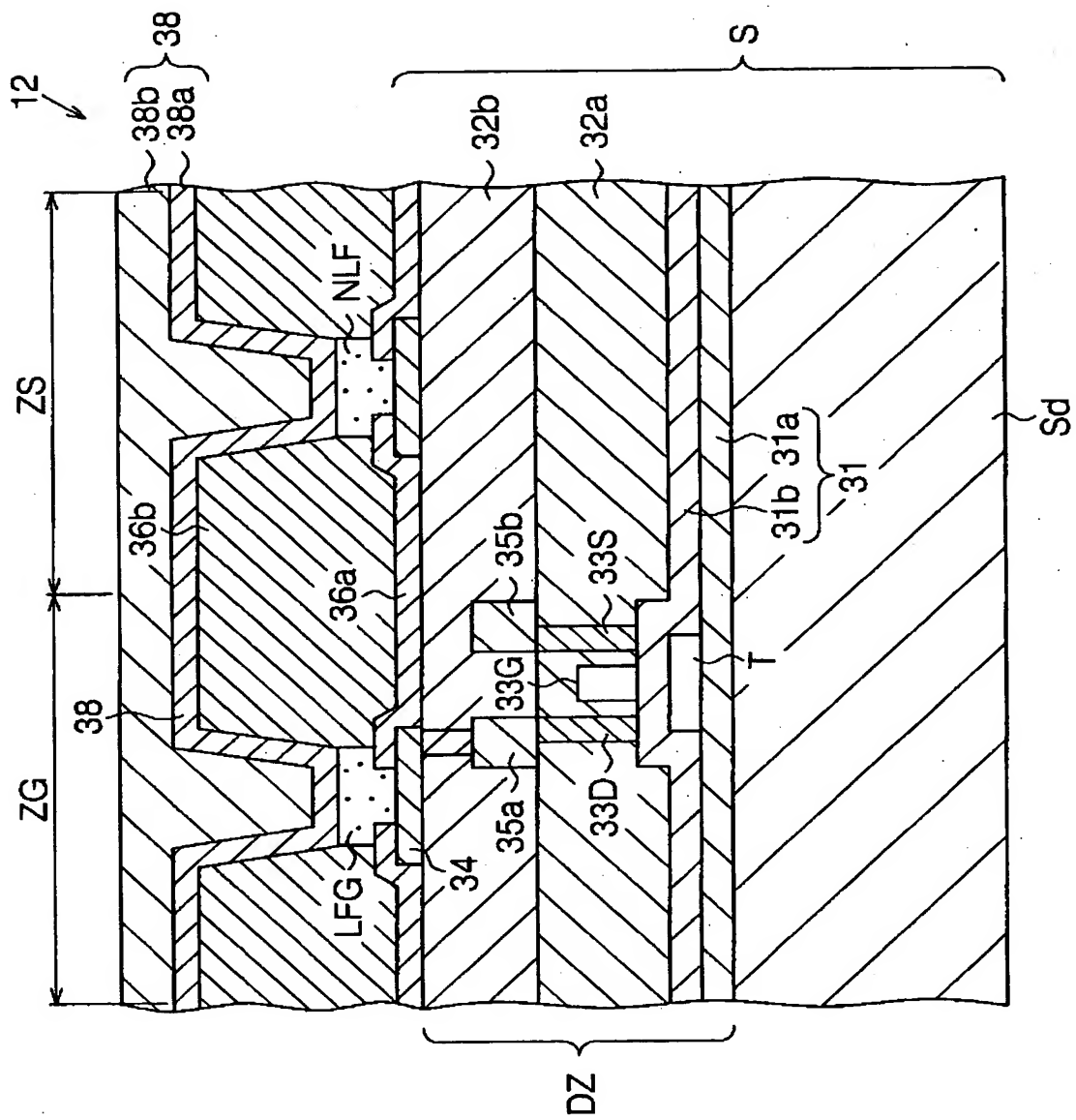


FIG.5

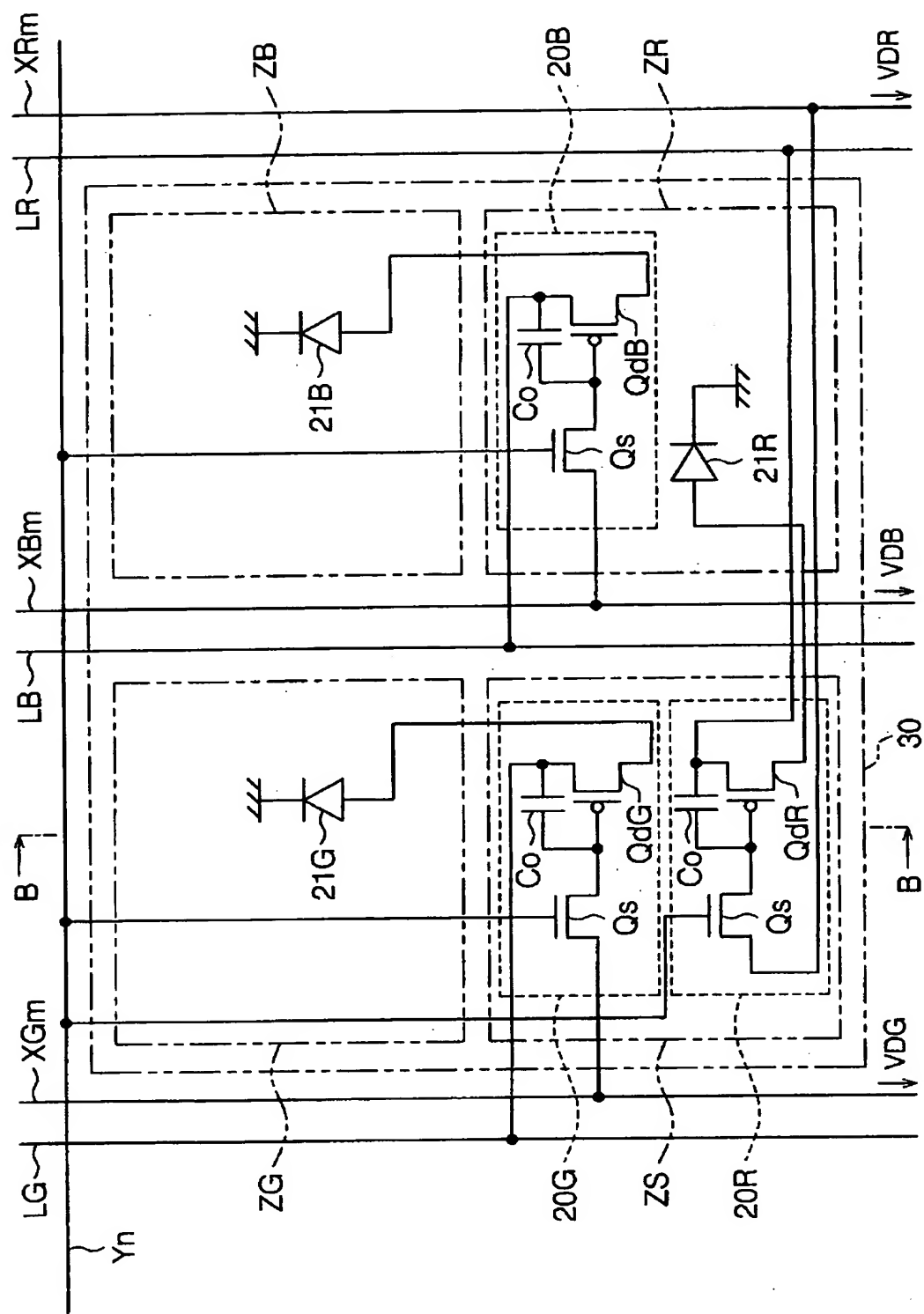


FIG.6

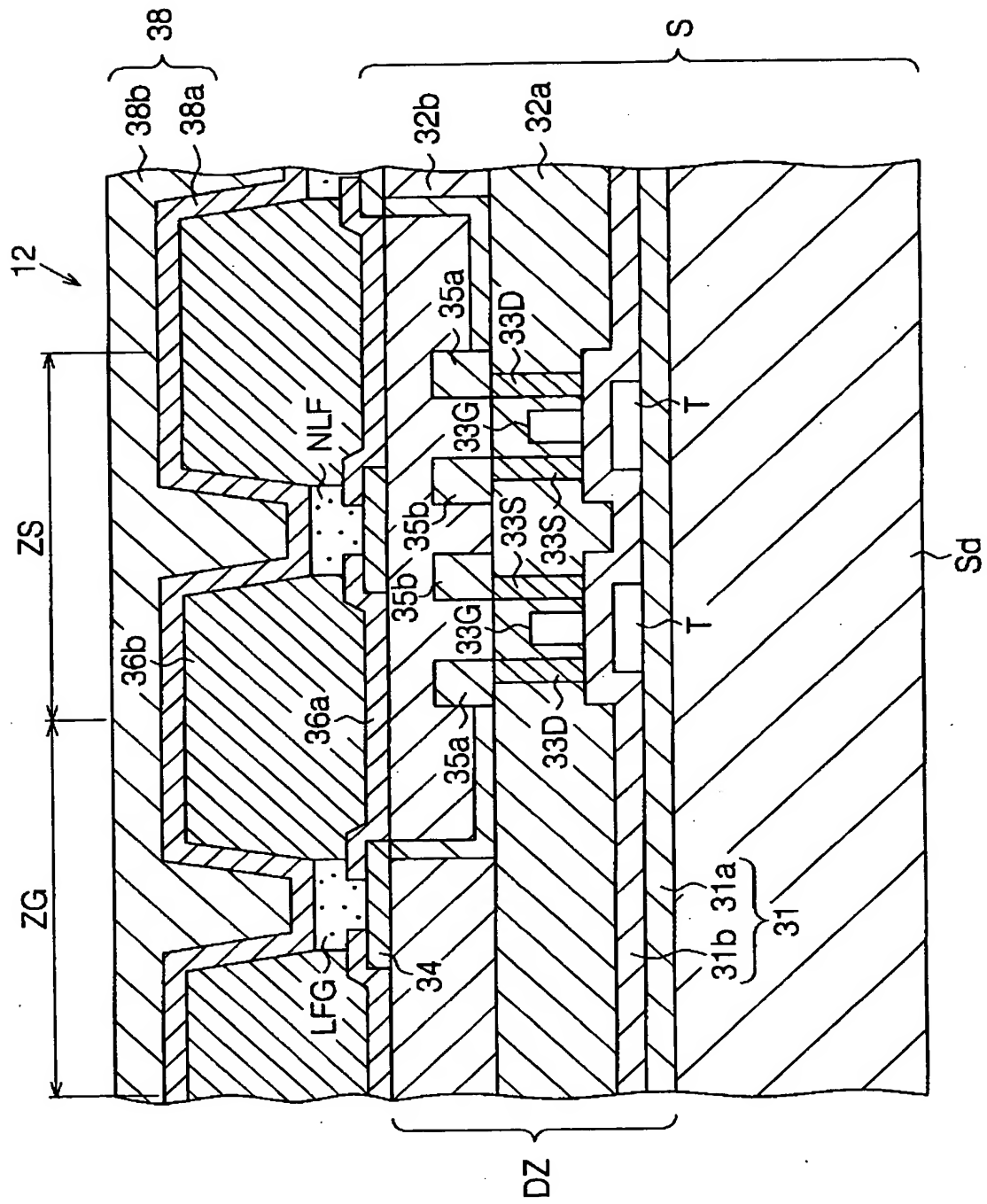


FIG.7

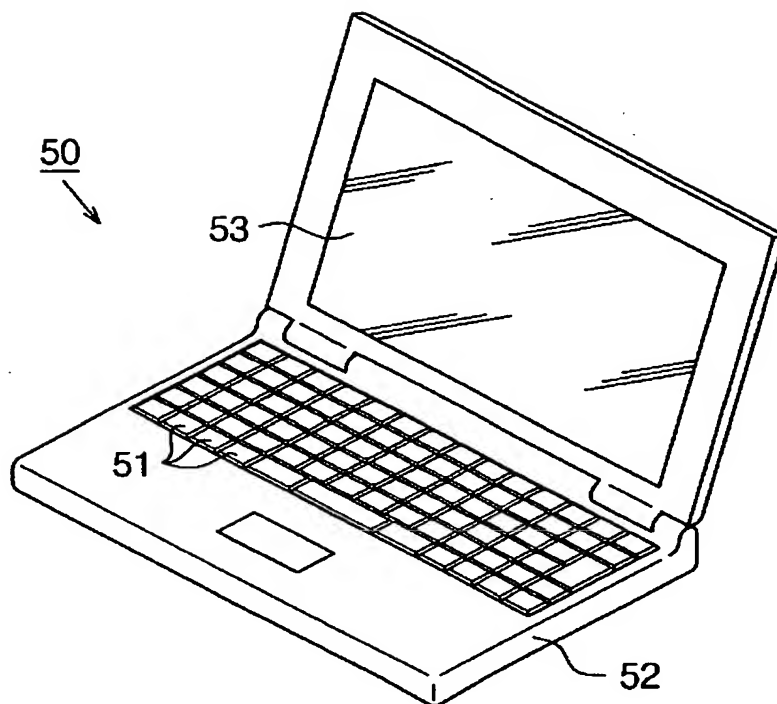


FIG.8

